Product Specification

QNM50P03AY

30V P-Channel MOSFET

FEATURES

- -30V, -40A

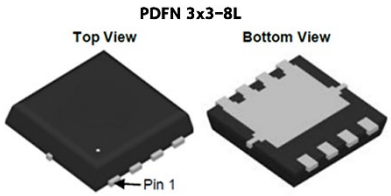
  $R_{DS(ON)}$ Typ = 7.4mΩ @ V_{GS} = -10V

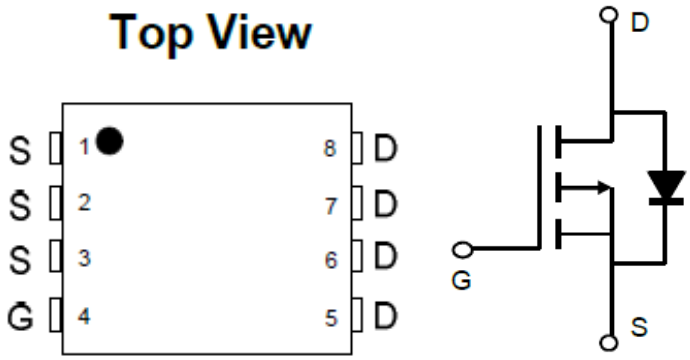
  $R_{DS(ON)}$ Typ = 13.5mΩ @ V_{GS} = -4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free
- 100% UIS TESTED
- 100% ΔVds TESTED

Applications

- PWM Applications
- Load Switch
- Power Management

Pin Description





NO.	Symbol	Description
1	S	SOURCE
2	S	SOURCE
3	S	SOURCE
4	G	GATE
5	D	DRAIN
6	D	DRAIN
7	D	DRAIN
8	D	DRAIN

Absolute Maximum Ratings

(@ T_C = 25℃ unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		-30	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C=25℃	-40	A
		T_C=100℃	-24	
I_{DM}	Pulsed Drain Current (1)		-160	A
E_{AS}	Single Pulsed Avalanche Energy (2)		56	mJ
P_D	Power Dissipation	T_C = 25℃	26	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		4.8	℃/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	℃

Electrical Characteristics

(T_J = 25℃ unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D=-250uA,V_{GS}=0V	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V,V_{GS}=0V	-	-	1.0	uA
I_{GSS}	Gate-Body Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	-1	-1.6	-2.2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS}=-10V, I_D=-15A	-	7.4	9.6	mΩ
		V_{GS}=-4.5V, I_D=10A	-	13.5	15.3	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS}=0V,V_{DS}=-15V, f=1MHz	-	1390	-	pF
C_{oss}	Output Capacitance		-	251	-	pF
C_{rss}	Reverse Transfer Capacitance		-	217	-	pF
Q_g	Total Gate Charge	V_{GS}=0~-10V V_{DS}=-15V, I_D=-20A	-	25	-	nC
Q_{gs}	Gate Source Charge		-	4	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	5.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS}=-10V,V_{DD}=-15V I_D=-20A, R_{GEN}=3Ω	-	11	-	ns
t_r	Turn-On Rise Time		-	17	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	60	-	ns
t_f	Turn-Off Fall Time		-	45	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-40	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-160	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=-15A	-	-	-1.2	V
t_{rr}	Body Diode Reverse Recovery Time	I_F=-20A, di/dt=100A/us	-	15	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	6	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25℃, V_{DD}=-15V, V_G=-10V, R_G=25Ω, L=0.5mH, I_{AS}=-15A

3. Pulse Test: Pulse Width≤300us, Duty Cycle≤0.5%.

Test Circuit-P

Figure 1: Gate Charge Test Circuit & Waveform

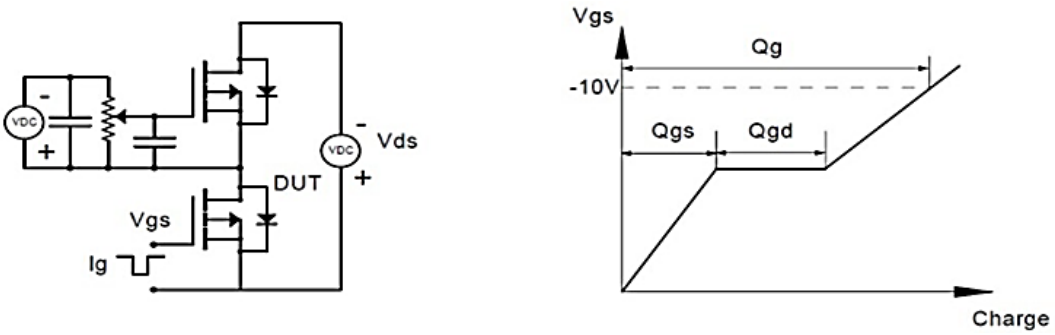


Figure 2: Resistive Switching Test Circuit & Waveform

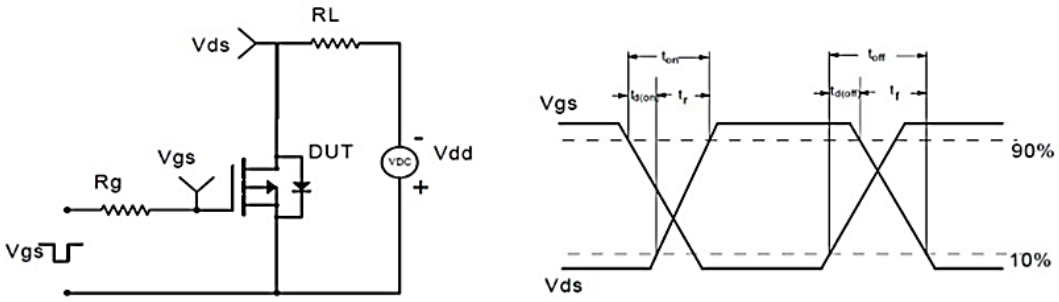


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

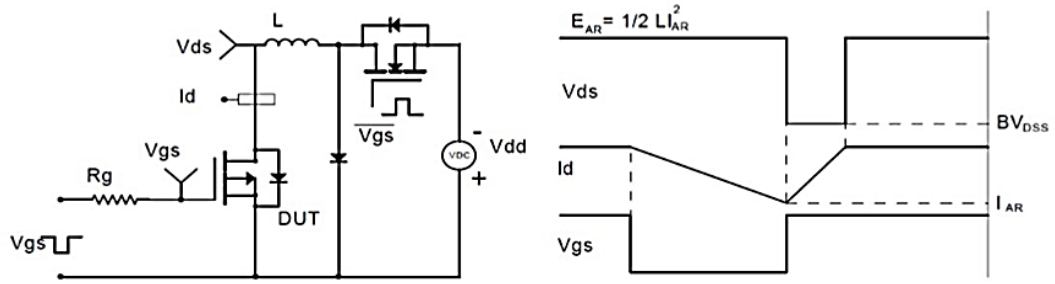
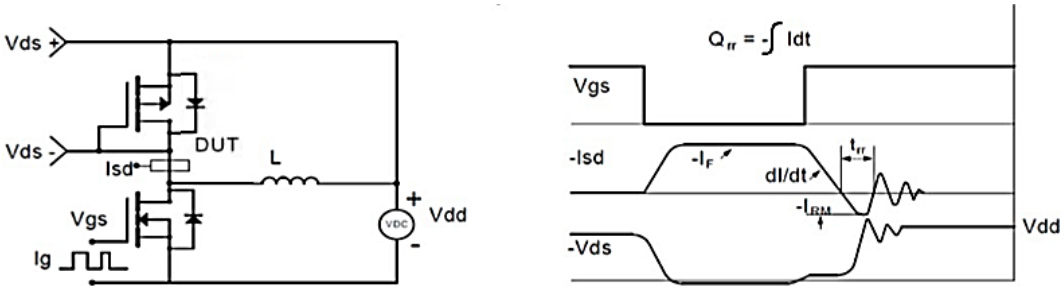
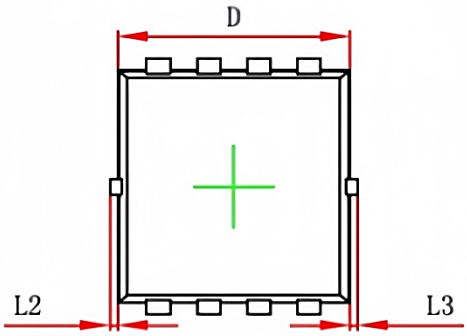


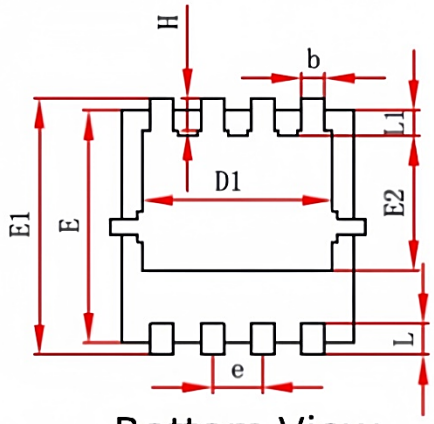
Figure 4: Diode Recovery Test Circuit & Waveform



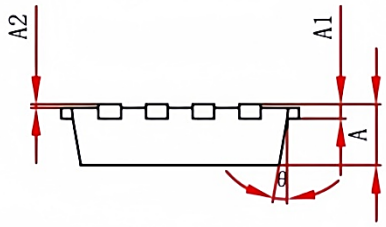
Package Mechanical Data(PDFN 3x3-8)



Top View

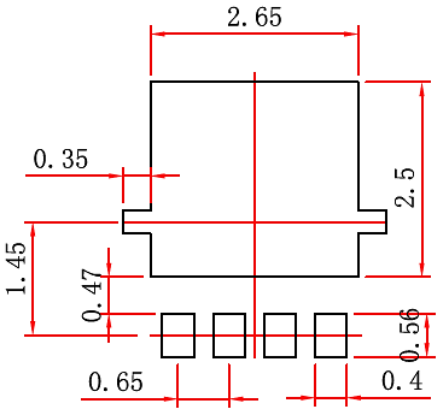


Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°



Note:

1. Controlling dimension: in millimeters.

2. General tolerance: ±0.05mm.

3. The pad layout is for reference purposes only.

Ordering information

Order Code	Package	V_{DS}(V)	I_D(A)	$R_{DS(ON)}$(mΩ)	
QNM50P03AY	PDFN 3x3-8	-30	-40	V_{GS}=-10V	7.4
				V_{GS}=-4.5V	13.5